NSN 5962-01-168-5840

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View Online at https://aerobasegroup.com/nsn/5962-01-168-5840

Body Length:
0.960 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
0.185 inches
Maximum Power Dissipation Rating:
715.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and programmable and schottky and monolithic
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
12 input
Case Outline Source And Designator:
D-6 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
125.00 nanoseconds propagation delay time, low to high level output and 125.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
18 printed circuit
Shelf Life:
N/a

Vec - demil/mli

Unit Of Measure:

Demilitarization:

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